

INFORMATION REPORT

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S-E-C-R-E-T

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SUBJECT	East German Germanium Point-Contact Transistor Types	DATE DISTR.	31 March 1955	
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1. The following table lists the types of germanium point-contact transistors developed by VEB Werk fuer Bauelemente der Nachrichtentechnik "Carl von Ossietzky" (formerly Dralowid) in Teltow.
2. There are four types of transistors:
 - a. Transistors for the frequency ranges up to 1 MHz¹, 3 MHz and 6 MHz with a maximum output amplification of 17 decibels.
 - b. Transistors for the frequency ranges up to 1 MHz, 3 MHz and 6 MHz with a maximum output amplification of 20 decibels.
 - c. Circuit transistors.
 - d. Oscillator transistors.

Types of Dralowid Transistors

a. Maximum output amplification of 17 decibels:

<u>Type</u>	<u>1NC-010</u>	<u>1NC-011</u>	<u>1NC-012</u>
Critical frequency	up to 1MHz	up to 3 MHz	Up to 6 MHz
Mean emitter voltage, in volt	0.2	0.2	0.1
Mean emitter current in milli-ampere	1	1	1
Maximum emitter current in milli-ampere	5	5	5
Mean collector voltage in volt	-15	-15	-15
Maximum collector voltage in volt	-50	-50	-50
Mean collector current in milli-ampere	-3	-3	-3
Maximum collector current in milli-ampere	-5	-5	-5
Maximum collector dissipation in milli-watt	120	120	120
Mean voltage amplification	50	50	50
Maximum voltage amplification	85	85	85
Mean output amplification in decibels	15	15	15
Maximum output amplification in decibels	17	17	17
Mean short circuit stability	0.5	0.5	0.5
Maximum short circuit stability	0.7	0.7	0.7

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STATE	#x	ARMY	#x	NAVY	x	AIR	#x	FBI	AEC	DST	Ev	x	ORR	Ev	x
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Type	1NC-010	1NC-011	1NC-012
Critical frequency in MHz	equal or more than 1	equal or more than 1	equal or more than 1
Mean input resistance in Ohm	200	200	200
Mean output resistance in Kilo-Ohm	10	10	10
Maximum admissible ambient temperature in centrigrades	+40	+40	+40
Maximum shakeproofness (Schuettelfestigkeit) in g	30	30	30

b. Maximum output amplification of 20 decibels:

Type	1NC-020	1NC-021	1NC-022
Critical frequency	up to 1 MHz	up to 3 MHz	up to 6 MHz
Mean emitter voltage, in volt	0.2	0.2	0.2
Mean emitter current in milli-ampere	1	1	1
Maximum emitter current in milli-ampere	5	5	5
Mean collector voltage in volt	-15	-15	-15
Maximum collector voltage in volt	-50	-50	-50
Mean collector current in milli-ampere	-3	-3	-3
Maximum collector current in milli-ampere	-5	-5	-5
Maximum collector dissipation in milli-watt	120	120	100
Mean voltage amplification	70	70	70
Maximum voltage amplification	120	120	120
Mean output amplification in decibels	19	19	19
Maximum output amplification in decibels	20	20	20
Mean short circuit stability	0.5	0.5	0.5
Maximum short circuit stability	0.7	0.7	0.7
Critical frequency in MHz	equal or more than 1	equal or more than 1	equal or more than 1
Mean input resistance in Ohm	200	200	200
Mean output resistance in kilo-Ohm	10	10	10
Maximum admissible ambient temperature in centrigrades	+40	+40	+40
Maximum shakeproofness in g	30	30	30

c. Circuit transistors

Type	2NC-010
Mean emitter voltage, in volt	0.2
Mean emitter current in milli-ampere	1
Maximum emitter current in milli-ampere	5
Mean collector voltage in volt	-15
Maximum collector voltage in volt	-50
Mean collector current in milli-ampere	-3
Maximum collector current in milli-ampere	-8
Maximum collector dissipation in milli-watt	150
Maximum voltage amplification	40
Mean output amplification in decibels	11
Maximum output amplification in decibels	13
Mean short circuit stability	0.4
Maximum short circuit stability	0.6
Mean input resistance in Ohm	200
Mean output resistance in kilo-Ohm	10
Maximum admissible ambient temperature in centrigrades	+40
Maximum shakeproofness in g	30

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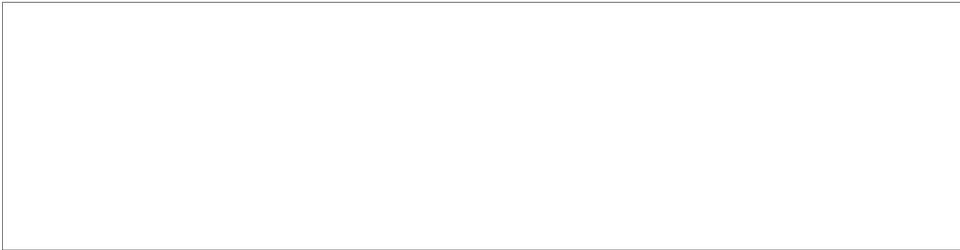
d. Oscillator transistors

<u>Type</u>	<u>3NC-070</u>
Mean emitter voltage, in volt	0.1
Mean emitter current in milli-ampere	1
Maximum emitter current in milli-ampere	5
Mean collector voltage in volt	-15
Maximum collector voltage in volt	-50
Mean collector current in milli-ampere	-2
Maximum collector current in milli-ampere	-4
Maximum collector dissipation in milli-watt	120
Mean voltage amplification	70
Maximum voltage amplification	120
Mean output amplification in decibels	18
Maximum output amplification in decibels	20
Maximum short circuit stability	0.8
Maximum short circuit stability	0.9
Critical frequency in MHz	equal or more than 10
Mean input resistance in Ohm	200
Mean output resistance in kilo-Ohm	10
Maximum admissible ambient temperature in centigrades	+40
Maximum shakeproofness in g	30



Comment: MHz (Megahertz) = megacycles (mcs).

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